FJE3303H1TU Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	FJE3303H1TU-DG
Manufacturer	onsemi
Manufacturer Product Number	FJE3303H1TU
Description	TRANS NPN 400V 1.5A TO126-3
Detailed Description	Bipolar (BJT) Transistor NPN 400 V 1.5 A 4MHz 20 W Through Hole TO-126-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
FJE3303H1TU	onsemi
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	1.5 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
400 V	3V @ 500mA, 1.5A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
10µA (ICBO)	8 @ 500mA, 2V
Power - Max:	Frequency - Transition:
20 W	4MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-225AA, TO-126-3	TO-126-3
Base Product Number:	
FJE3303	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	Not Applicable
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Is Now Part of

ON Semiconductor®

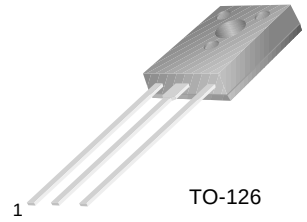
To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FJE3303

High Voltage Fast-Switching NPN Power Transistor

- High Voltage Capability
- High Switching Speed
- Suitable for Electronic Ballast and Switching Regulator



TO-126

1. Emitter 2.Collector 3.Base

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current (DC)	1.5	A
I_{CP}	Collector Current (Pulse) *	3	A
I_B	Base Current (DC)	0.75	A
I_{BP}	Base Current (Pulse) *	1.5	A
P_C	Collector Dissipation (T_C = 25°C)	20	W
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	-65 ~ 150	°C

* Pulse Test: Pulse Width = 5ms, Duty Cycle ≤ 10%

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max	Units
BV_{CBO}	Collector-Base Breakdwon Voltage	I_C = 500μA, I_E = 0	700			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5mA, I_B = 0	400			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 500μA, I_C = 0	9			V
I_{CBO}	Collector Cut-off Current	V_{CB} = 700V, I_E = 0			10	μA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 9V, I_C = 0			10	μA
h_{FE1} h_{FE2}	DC Current Gain *	V_{CE} = 2V, I_C = 0.5A V_{CE} = 2V, I_C = 1.0A	8 5		21	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 0.5A, I_B = 0.1A I_C = 1.0A, I_B = 0.25A I_C = 1.5A, I_B = 0.5A			0.5 1.0 3.0	V V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 0.5A, I_B = 0.1A I_C = 1.0A, I_B = 0.25A			1.0 1.2	V V
f_T	Current Gain Bandwidth Product	V_{CE} = 10V, I_C = 0.1A	4			MHz
C_{ob}	Output Capacitance	V_{CB} = 10V, f = 0.1MHz		21		pF
t_{ON}	Turn On Time	V_{CC} = 125V, I_C = 1A I_{B1} = 0.2A, I_{B2} = -0.2A R_L = 125Ω			1.1	μs
t_{STG}	Storge Time				4.0	μs
t_F	Fall Time				0.7	μs

* Pulse Test: PW ≤ 300μs, Duty Cycle ≤ 2%

h_{FE} Classification

Classification	H1	H2
h_{FE1}	8 ~ 16	14 ~ 21

Typical Performance Characteristics

Figure 1. Static Characteristic

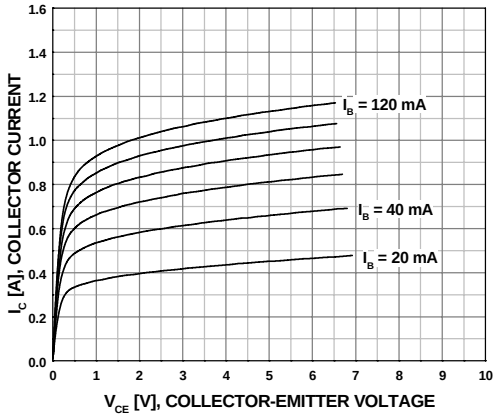


Figure 2. DC Current Gain

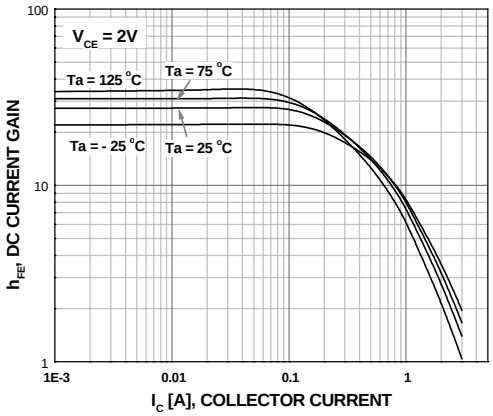


Figure 3. Collector-Emitter Saturation Voltage

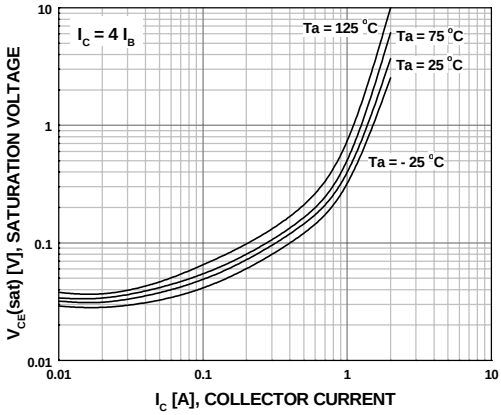


Figure 4. Base-Emitter Saturation Voltage

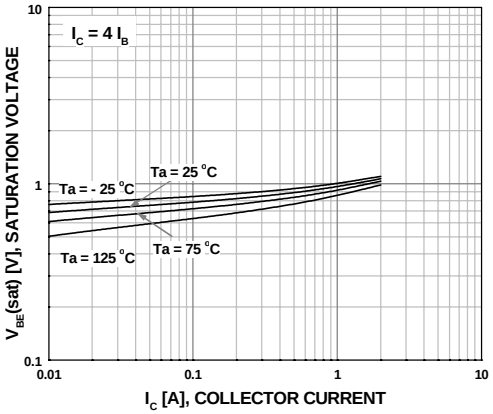


Figure 5. Resistive Load Switching Time

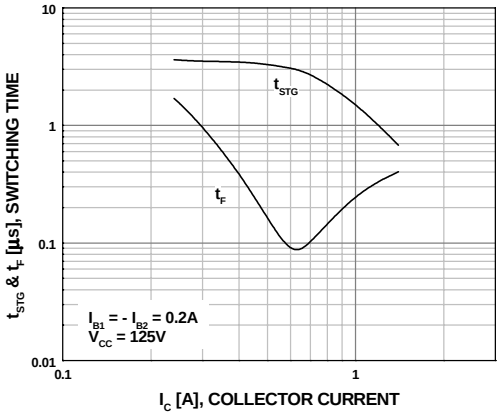
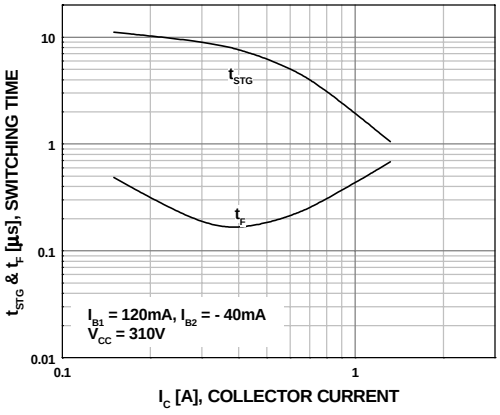


Figure 6. Resistive Load Switching Time



Typical Performance Characteristics (Continued)

Figure 7. Forward Biased Safe Operating Area

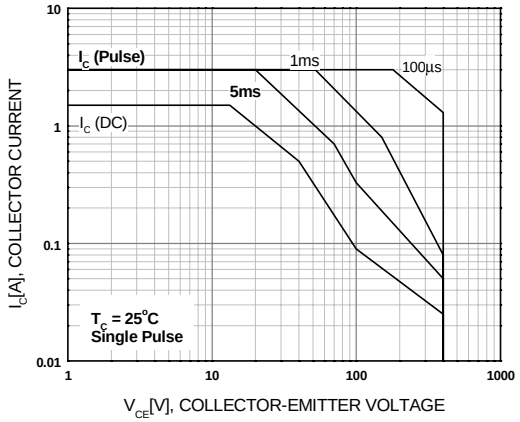


Figure 8. Reverse Biased Safe Operating Area

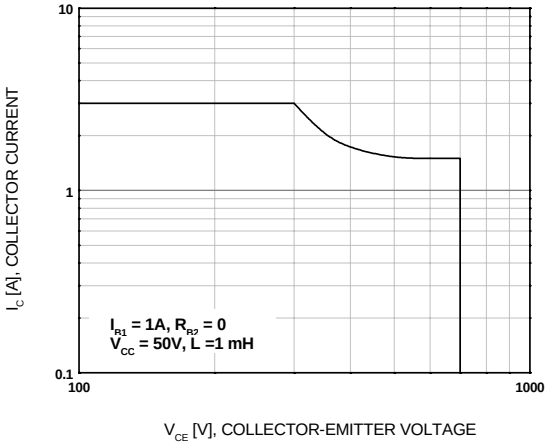
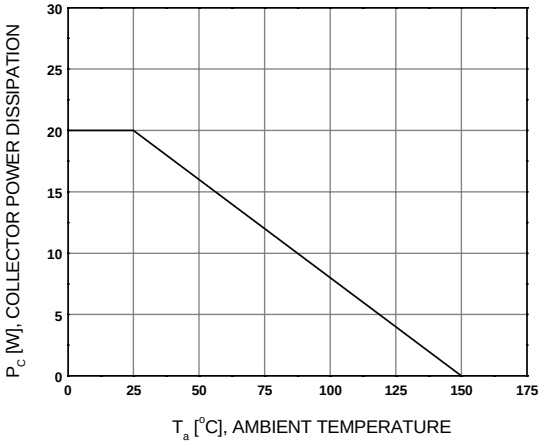
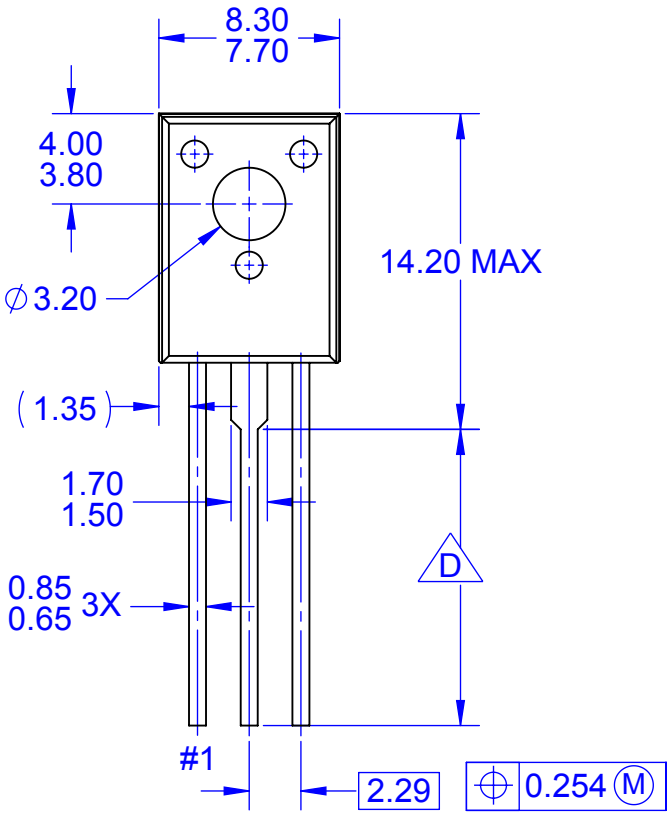
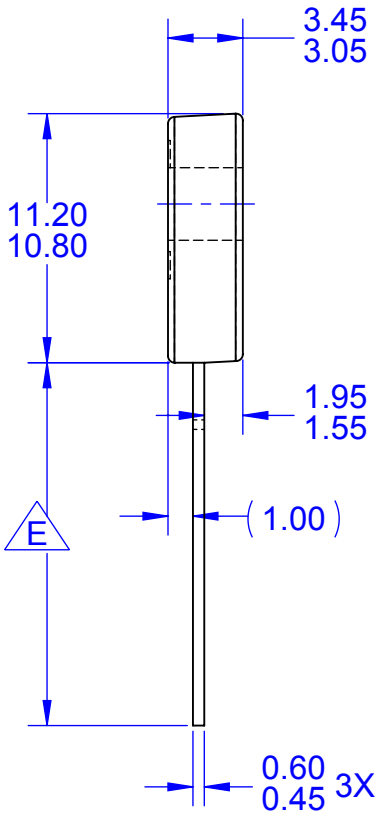


Figure 9. Power Derating

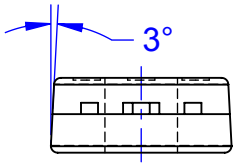




TOP VIEW



SIDE VIEW



FRONT VIEW

PRODUCTION CODE	TERMINAL LENGTH "D"	TERMINAL LENGTH "E"
TSSTU	3.45 - 4.05	6.45-7.45
TSTU	2.36 - 2.96	5.36-6.36
NONE (STD LENGTH)	12.76 - 13.36	15.76-16.76

NOTES:

A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE
B. ALL DIMENSIONS ARE IN MILLIMETERS
C. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS

△D FOR TERMINAL LENGTH "D", REFER TO TABLE

△E FOR TERMINAL LENGTH "E", REFER TO TABLE

F. DRAWING FILENAME: MKT-TO126AArev2

FAIRCHILD ™

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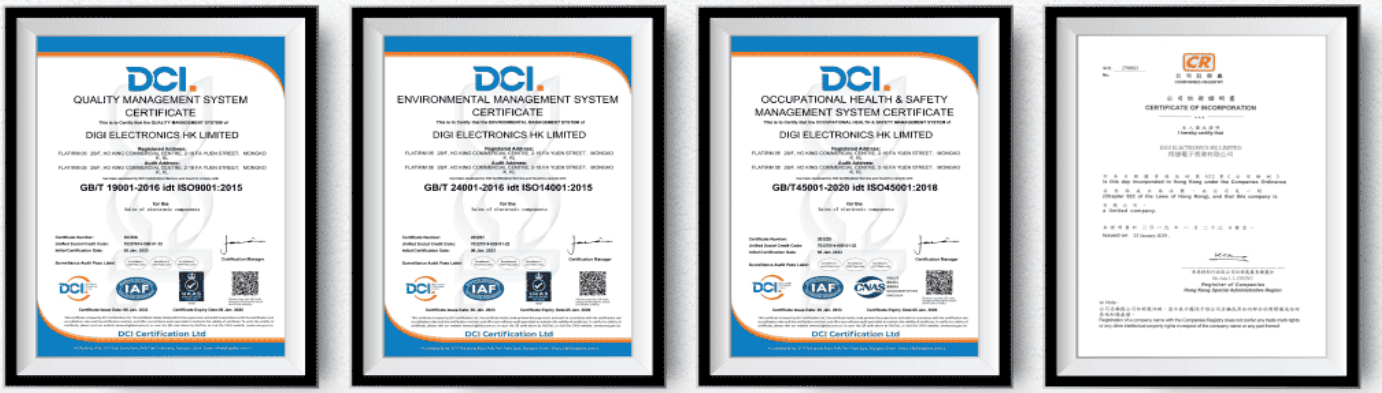

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